

IN THE CLAIMS:

A₂ 4. (Amended) The electrode according to claim 2, wherein a shower head portion that supplies a gas is provided on a lower surface of the base metal.

5. (Amended) The electrode according to claim 2, wherein the electrode is configured so that a high frequency voltage is applied thereto.

A₃ 8. (Amended) The susceptor according to claim 6, wherein the upper ceramic-metal composite and the electrostatic chuck are brazed together.

9. (Amended) The susceptor according to claim 6, wherein the upper ceramic-metal composite and the electrostatic chuck are forge-welded together.

10. (Amended) The susceptor according to claim 6, wherein the upper ceramic-metal composite and the electrostatic chuck are adhered together.

11. (Amended) The susceptor according to claim 6, wherein the susceptor is configured so that a high frequency voltage is applied thereto.

A₄ 15. (Amended) The plasma processing apparatus according to claim 12, wherein a shower head portion for supplying a gas is provided on a lower surface of the base metal.

A₅ 18. (Amended) The plasma processing apparatus according to claim 16, wherein the susceptor is provided with heat transfer gas passages that supplies a heat transfer gas to a surface of the electrostatic, the passage passing through the susceptor.

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conclude

19. (Amended) The plasma processing apparatus according to claim 16, wherein the upper ceramic-metal composite and the electrostatic chuck are brazed together.

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20. (Amended) The plasma processing apparatus according to claim 16, wherein the upper ceramic-metal composite and the electrostatic chuck are forge-welded together.

21. (Amended) The plasma processing apparatus according to claim 16, wherein the upper ceramic-metal composite and the electrostatic chuck are adhered together.

24. (New) The electrode according to claim 1, wherein a shower head portion that supplies a gas is provided on a lower surface of the base metal.

25. (New) The electrode according to claim 1, wherein the electrode is configured so that a high frequency voltage is applied thereto.

26. (New) The plasma processing apparatus according to claims 13, wherein a shower head portion for supplying a gas is provided on a lower surface of the base metal.

REMARKS

Claims 1- 26 are pending in this application. The presentation of a clean set of claims is permitted under new rule 37 C.F.R. 1.121 (c)(3), effective November 7, 2000. Claims 4-5, 8-11, 15, and 18-21 have been amended to remove multiple dependencies from the claims. An amended form of claims 4-5,